

ST9609/Dr.St

Abstract:

The invention relates to a process for producing a silicon single crystal by the Czochralski method, and to a heater which is intended for heating a silicon-filled crucible and is arranged below the crucible. The process is characterized in that energy is delivered to the melt at least some of the time inductively using a coiled heater arranged under the crucible. The heater is designed in ~~in~~ [sic] the form of a wound coil.

